100V N-Channel MOS FETs

General Description

These N-Channel enhancement mode power field effect transistors are using trench DMOS technology. This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode. These devices are well suited for high efficiency fast switching applications.

BVDSS	RDSON	ID
100V	200mΩ	2A

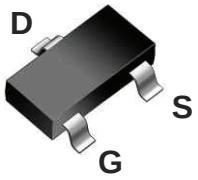
Features

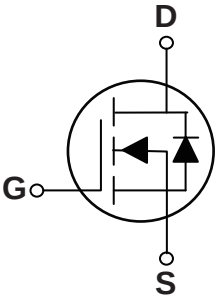
- *100V,2A, RDS(ON) =200mΩ@VGS = 10V*
- *Improved dv/dt capability*
- *Fast switching*
- *100% EAS Guaranteed*

Applications

- *Networking*
- *Load Switch*
- *LED applications*

SOT23-3S Pin Configuration





Absolute Maximum Ratings **Tc=25℃ unless otherwise noted**

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	100	V
V_{GS}	Gate-Source Voltage	±20	V
I_D	Drain Current – Continuous (T_C=25℃)	2	A
	Drain Current – Continuous (T_C=100℃)	1.3	A
I_{DM}	Drain Current – Pulsed[1]	8	A
P_D	Power Dissipation (T_C=25℃)	1.56	W
	Power Dissipation – Derate above 25℃	0.012	W/℃
T_{STG}	Storage Temperature Range	-50 to 150	℃
T_J	Operating Junction Temperature Range	-50 to 150	℃

Thermal Characteristics

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction to ambient	---	80	℃/W

Electrical Characteristics (T_J=25℃)

Off Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V , I_D=250uA	100	---	---	V
$\triangle BV_{DSS}/\triangle T_J$	BV_{DSS} Temperature Coefficient	Reference to 25℃ , I_D=1mA	---	0.10	---	V/℃
I_{DSS}	Drain-Source Leakage Current	V_{DS}=100V , V_{GS}=0V , T_J=25℃	---	---	1	uA
		V_{DS}=80V , V_{GS}=0V , T_J=125℃	---	---	10	uA
I_{GSS}	Gate-Source Leakage Current	V_{GS}=± 20V , V_{DS}=0V	---	---	± 100	nA

On Characteristics

$R_{DS(ON)}$	Static Drain-Source On-Resistance	V_{GS}=10V , I_D=2A	---	161	200	mΩ
		V_{GS}=4.5V , I_D=1A	---	169	210	mΩ
$V_{GS(th)}$	Gate Threshold Voltage	V_{GS}=V_{DS} , I_D =250uA	1.2	1.8	2.5	V
$\triangle V_{GS(th)}$	$V_{GS(th)}$ Temperature Coefficient		---	-4	---	mV/℃
gfs	Forward Transconductance	V_{DS}=10V , I_D=1A	---	5	---	S

Dynamic and switching Characteristics

Q_g	Total Gate Charge[2,3]	V_{DS}=50V , V_{GS}=10V , I_D=2A	---	13.4	21	nC
Q_{gs}	Gate-Source Charge[2,3]		---	2.9	6	
Q_{gd}	Gate-Drain Charge[2,3]		---	1.7	4	
$T_{d(on)}$	Turn-On Delay Time[2,3]	V_{DD}=30V , V_{GS}=10V , R_G=3.3Ω , I_D=1A	---	1.6	3	ns
T_r	Rise Time[2,3]		---	6.6	13	
$T_{d(off)}$	Turn-Off Delay Time[2,3]		---	11.5	22	
T_f	Fall Time[2,3]		---	3.6	7	
C_{iss}	Input Capacitance	V_{DS}=50V , V_{GS}=0V , F=1MHz	---	820	1190	pF
C_{oss}	Output Capacitance		---	35	55	
C_{rss}	Reverse Transfer Capacitance		---	20	30	
R_g	Gate resistance	V_{GS}=0V, V_{DS}=0V, F=1MHz	---	1.3	2.6	Ω

Drain-Source Diode Characteristics and Maximum Ratings

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_S	Continuous Source Current	V_G=V_D=0V , Force Current	---	---	2	A
I_{SM}	Pulsed Source Current		---	---	8	A
V_{SD}	Diode Forward Voltage	V_{GS}=0V , I_S=1A , T_J=25℃	---	---	1	V

Note :
1. Repetitive Rating : Pulsed width limited by maximum junction temperature.
2. The data tested by pulsed , pulse width ≦ 300us , duty cycle ≦ 2%.
3. Essentially independent of operating temperature.

ELECTRICAL CHARACTERISTICS CURVES

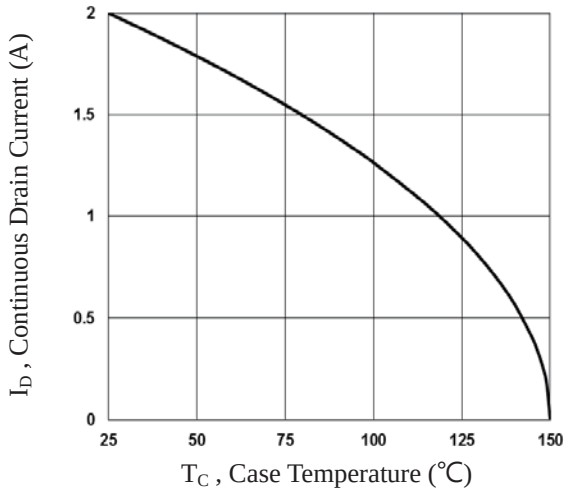


Fig.1 Continuous Drain Current vs. T_C

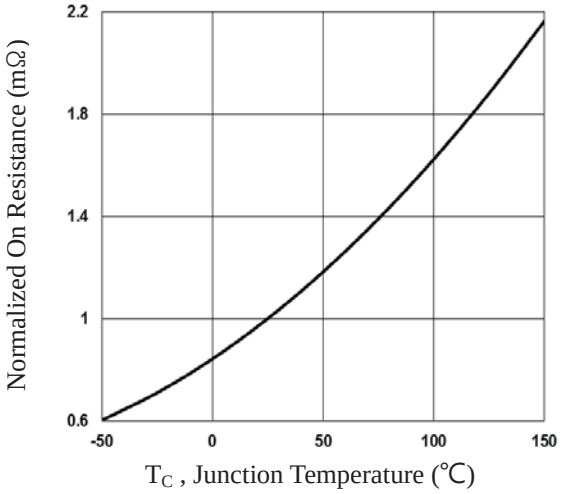


Fig.2 Continuous Drain Current vs. T_C

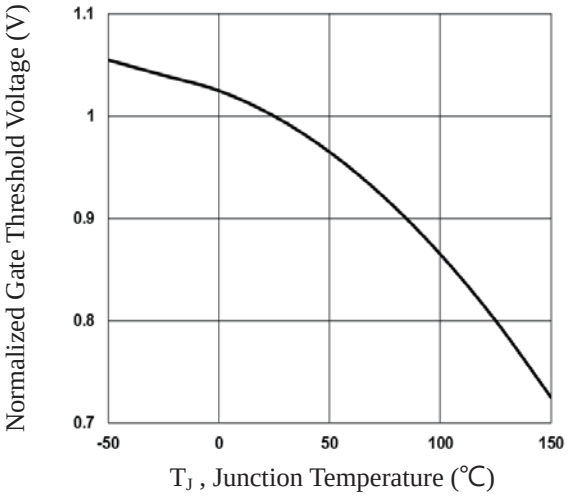


Fig.3 Normalized V_{th} vs. T_J

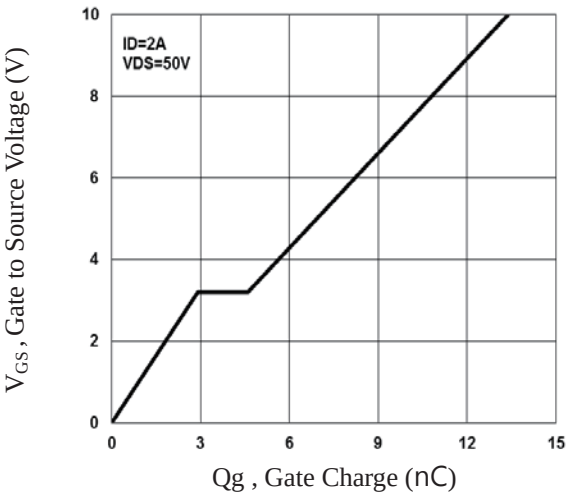


Fig.4 Gate Charge Waveform

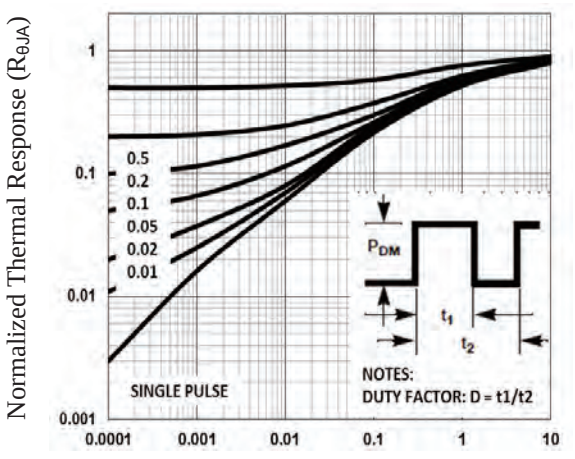


Fig.5 Normalized Transient Impedance

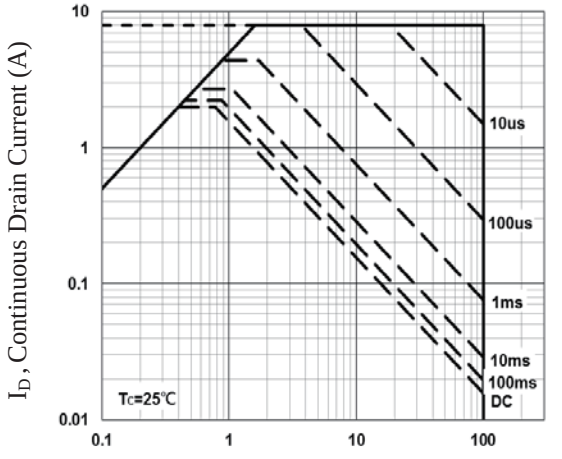


Fig.6 Maximum Safe Operation Area

ELECTRICAL CHARACTERISTICS CURVES（Con.）

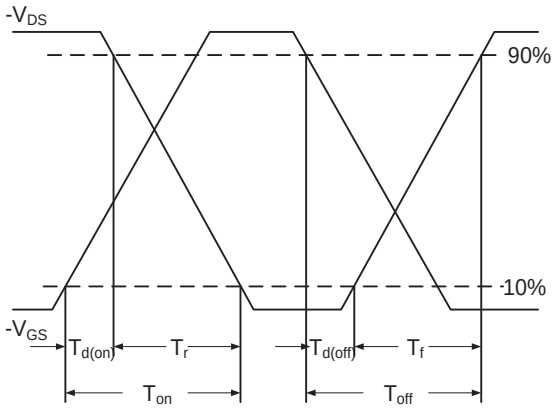


Fig.7 Switching Time Waveform

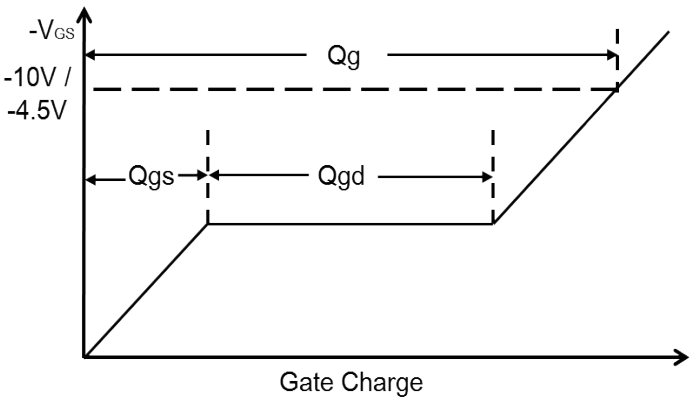
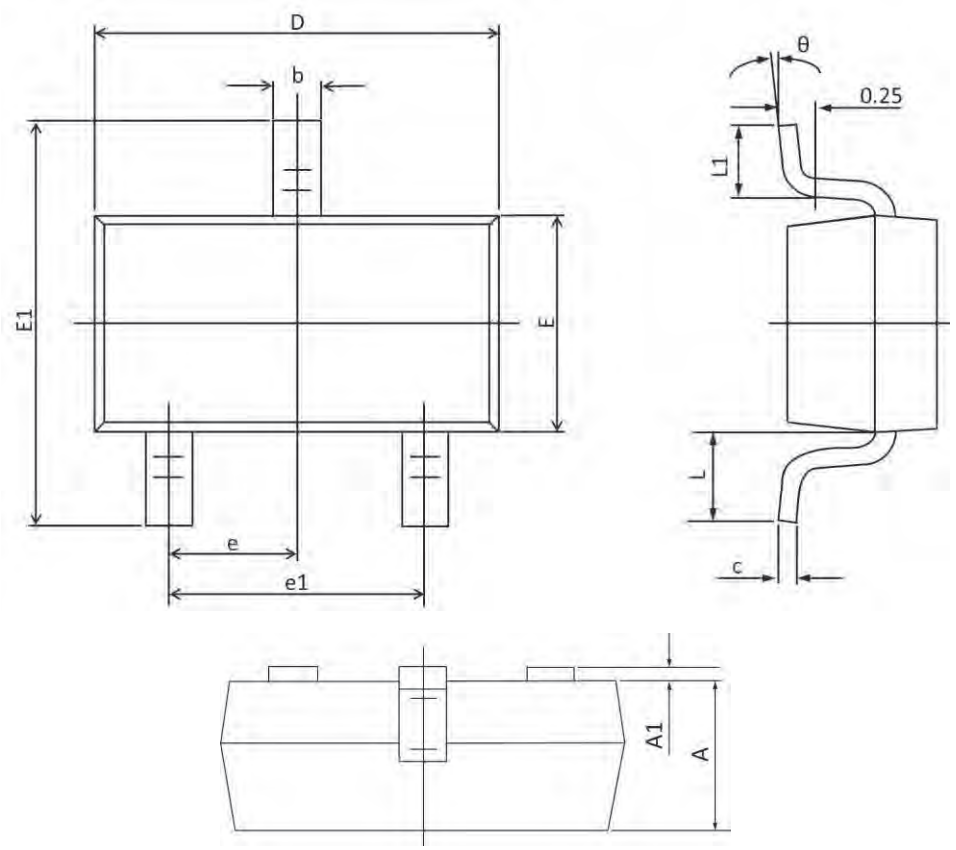


Fig.8 Gate Charge Waveform



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	0.900	1.000	0.035	0.039
A1	0.000	0.100	0.000	0.004
b	0.300	0.500	0.012	0.020
c	0.090	0.110	0.003	0.004
D	2.800	3.000	0.110	0.118
E	1.200	1.400	0.047	0.055
E1	2.250	2.550	0.089	0.100
e	0.950 TYP.		0.037 TYP.	
e1	1.800	2.000	0.071	0.079
L	0.550 REF.		0.022 REF.	
L1	0.300	0.500	0.012	0.020
θ	1°	7°	1°	7°